20 AMPERES

VOLTAGE CLAMPED

N-CHANNEL IGBT

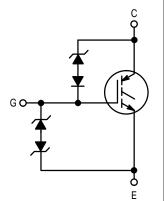
V_{CE(on)} = 1.9 VOLTS

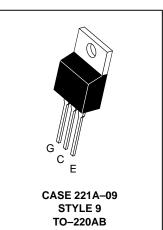
135 VOLTS (CLAMPED)

Product Preview SMARTDISCRETES™ Internally Clamped, N-Channel IGBT

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features Gate–Emitter ESD protection, Gate–Collector overvoltage protection from SMARTDISCRETES[™] monolithic circuitry for usage as an **Ignition Coil Driver**.

- Temperature Compensated Gate–Collector Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage to Interface Power Loads to Logic or Microprocessors
- Low Saturation Voltage
- High Pulsed Current Capability





MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	CLAMPED	Vdc
Collector–Gate Voltage	VCGR	CLAMPED	Vdc
Gate-Emitter Voltage	VGE	CLAMPED	Vdc
Collector Current — Continuous — Single Pulsed ($t_p = \pm 10 \ \mu s$)	IС IСМ	20 60	Adc Apk
Total Power Dissipation (TO–220) Derate Above 25°C	PD	150 1.0	Watts W/°C
Operating and Storage Temperature Range	TJ, Tstg	-55 to 175	°C
Single Pulse Collector–Emitter Avalanche Energy @ Starting T _J = 25° C (V _{CC} = 80 V, V _{GE} = 5 V, Peak I _L = 10 A, L = 10 mH)	EAS	500	mJ

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case – (TO–220) — Junction to Ambient	R _θ JC R _{θJA}	1.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds		260	°C
Mounting Torque, 6–32 or M3 screw	10 lbf∙in (1.13 N∙m)		

SMARTDISCRETES is a trademark of Motorola, Inc.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

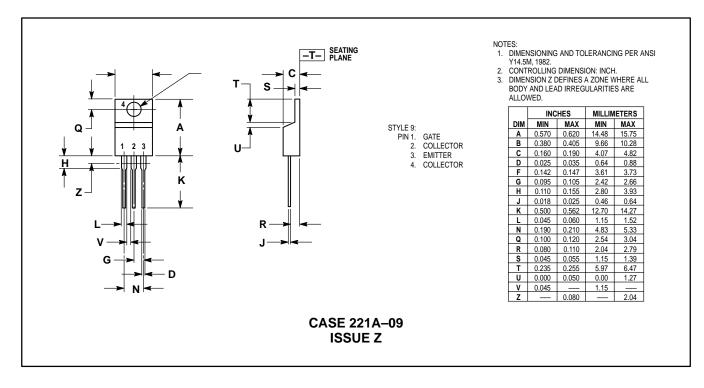


ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Cha	racteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•				
Clamp Voltage (I _{Clamp} = 10 mA, T _J = -40 to 1	50°C)	V(BR)CES	135			Vdc
Zero Gate Voltage Collector Curre (V _{CE} = 100 V, V _{GE} = 0 V) (V _{CE} = 100 V, V _{GE} = 0 V, T _J =		ICES			10 100	μΑ
Gate-Emitter Clamp Voltage (IG =	Gate–Emitter Clamp Voltage (I _G = 1 mA)		10			Vdc
Gate–Emitter Leakage Current ($V_{GE} = \pm 5 V$, $V_{CE} = 0 V$)		IGES	—	-	1.0	μΑ
ON CHARACTERISTICS (1)		•				
Gate Threshold Voltage ($V_{CE} = V_{GE}$, $I_C = 1 \text{ mA}$) Threshold Temperature Coefficient	ent (Negative)	VGE(th)	1.0	1.5 4.4	2.0	V mV/°C
$ Collector-Emitter On-Voltage \\ (V_{GE} = 5 V, I_C = 10 A) \\ (V_{GE} = 5 V, I_C = 10 Adc, T_J = 7 \\ $	175°C)	VCE(on)			1.9 1.8	V
Forward Transconductance (VCE	> 15 V, I _C = 10 A)	9fe	8.0	15	—	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance		C _{ies}	—	430	600	pF
Output Capacitance	(V _{CE} = 25 Vdc, V _{GE} = 0 Vdc, f = 1.0 MHz)	C _{oes}	—	182	250	
Transfer Capacitance		C _{res}	—	48	100	
SWITCHING CHARACTERISTICS	(1)	•				
Turn–On Delay Time		^t d(on)	—	TBD	TBD	ns
Rise Time	$(V_{CC} = 68 \text{ V}, \text{ I}_{C} = 20 \text{ A}, V_{GE} = 5 \text{ V}, \text{ R}_{G} = 9.1 \Omega)$	tr	—	TBD	TBD	1
Turn-Off Delay Time		^t d(off)	—	TBD	TBD	
Fall Time		tf	—	TBD	TBD	1
Total Gate Charge		QT	—	14	20	nC
Gate-Emitter Charge	$(V_{CC} = 108 \text{ V}, \text{ I}_{C} = 20 \text{ A}, \\ V_{GE} = 5 \text{ V})$	Q _{ge}	—	3.0	—	1
Gate-Collector Charge		Q _{gc}	_	6.0	_	1

(1) Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

PACKAGE DIMENSIONS



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